SI3129DV-T1-GE3 Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	SI3129DV-T1-GE3-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	SI3129DV-T1-GE3
Description	P-CHANNEL 80 V (D-S) MOSFET TSOP
Detailed Description	P-Channel 80 V 3.8A (Ta), 5.4A (Tc) 2W (Ta), 4.2W (Tc) Surface Mount 6-TSOP

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

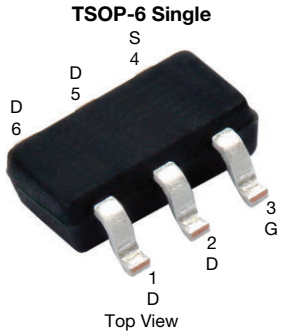
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SI3129DV-T1-GE3	Vishay Siliconix
Series:	Product Status:
TrenchFET®	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
80 V	3.8A (Ta), 5.4A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	82.7mOhm @ 3.8A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 250µA	18 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	805 pF @ 40 V
FET Feature:	Power Dissipation (Max):
-	2W (Ta), 4.2W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
6-TSOP	SOT-23-6 Thin, TSOT-23-6

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
ECCN:	HTSUS:
EAR99	8541.29.0095

P-Channel 80 V (D-S) MOSFET



Marking Code: BU

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

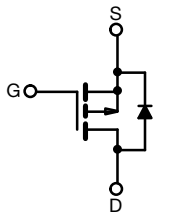
Pb-free

RoHS COMPLIANT

HALOGEN FREE

APPLICATIONS

- Power management for portable and consumer
  - Load switches
  - DC/DC converters



P-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-80
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.0827
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V	0.1242
Q_g typ. (nC)	5.6
I_D (A) [a]	-5.4
Configuration	Single

ORDERING INFORMATION	
Package	TSOP-6 Single
Lead (Pb)-free and halogen-free	Si3129DV-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-80	V
Gate-source voltage		V_{GS}	±20	
Continuous drain current (T_J = 150 °C)	T_C = 25 °C	I_D	-5.4	A
	T_C = 70 °C		-4.4	
	T_A = 25 °C		-3.8 [b, c]	
	T_A = 70 °C		-3.0 [b, c]	
Pulsed drain current (t = 300 µs)		I_{DM}	-20	
Continuous source-drain diode current	T_C = 25 °C	I_S	-3.5	
	T_A = 25 °C		-1.7 [b, c]	
Single pulse avalanche energy	L = 0.1 mH	I_{AS}	15	
		E_{AS}	11	
Maximum power dissipation	T_C = 25 °C	P_D	4.2	W
	T_C = 70 °C		2.7	
	T_A = 25 °C		2 [b, c]	
	T_A = 70 °C		1.3 [b, c]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient [b, d]	t ≤ 5 s	R_{thJA}	45	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30	

Notes

a. T_C = 25 °C
b. Surface mounted on 1" x 1" FR4 board
c. t = 5 s
d. Maximum under steady state conditions is 110 °C/W

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-80	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I_D = -10 mA	-	-115	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA	-	4.8	-	
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1.5	-	-2.5	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -80 V, V_{GS} = 0 V	-	-	-10	µA
		V_{DS} = -80 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-50	
On-state drain current [a]	$I_{D(on)}$	$V_{DS} \leq$ -5 V, V_{GS} = -10 V	-5	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -3.8 A	-	0.0689	0.0827	Ω
		V_{GS} = -4.5 V, I_D = -3.1 A	-	0.0994	0.1242	
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = -40 V, V_{GS} = 0 V, f = 1 MHz	-	805	-	pF
Output capacitance	C_{oss}		-	265	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Total gate charge	Q_g	V_{DS} = -40 V, V_{GS} = -10 V, I_D = -3.8 A	-	12	18	nC
		V_{DS} = -40 V, V_{GS} = -4.5 V, I_D = -3.8 A	-	5.6	8.4	
Gate-source charge	Q_{gs}		-	3.1	-	
Gate-drain charge	Q_{gd}		-	1.4	-	
Gate resistance	R_g	f = 1 MHz	0.8	4.4	8.8	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = -40 V, R_L = 13.3 Ω $I_D \cong$ -3 A, V_{GEN} = - 10 V, R_g = 1 Ω	-	15	30	ns
Rise time	t_r		-	8	16	
Turn-off delay time	$t_{d(off)}$		-	25	50	
Fall time	t_f		-	12	24	
Turn-on delay time	$t_{d(on)}$	V_{DD} = -40 V, R_L = 13.3 Ω $I_D \cong$ -3 A, V_{GEN} = - 4.5, R_g = 1 Ω	-	28	56	
Rise time	t_r		-	42	84	
Turn-off delay time	$t_{d(off)}$		-	24	48	
Fall time	t_f		-	15	30	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	T_C = 25 °C	-	-	-3.5	A
Pulse diode forward current	I_{SM}		-	-	-20	
Body diode voltage	V_{SD}	I_S = -3 A, V_{GS} = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t_{rr}	I_F = -3 A, dI/dt = 100 A/µs, T_J = 25 °C	-	38	57	ns
Body diode reverse recovery charge	Q_{rr}		-	50	75	nC
Reverse recovery fall time	t_a		-	26	-	ns
Reverse recovery rise time	t_b		-	12	-	

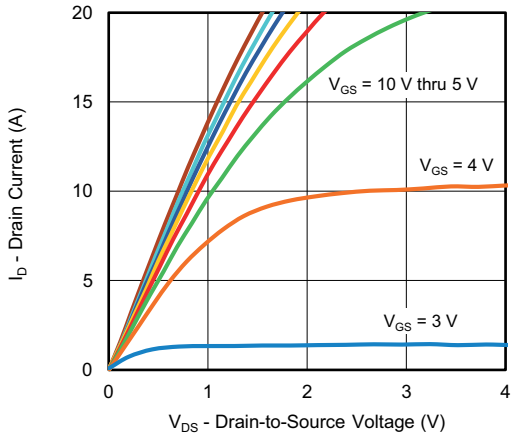
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %

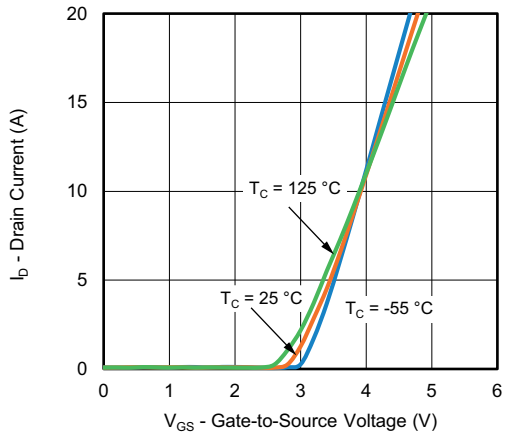
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

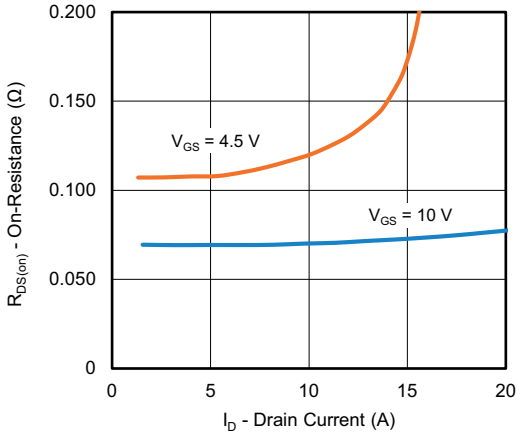
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



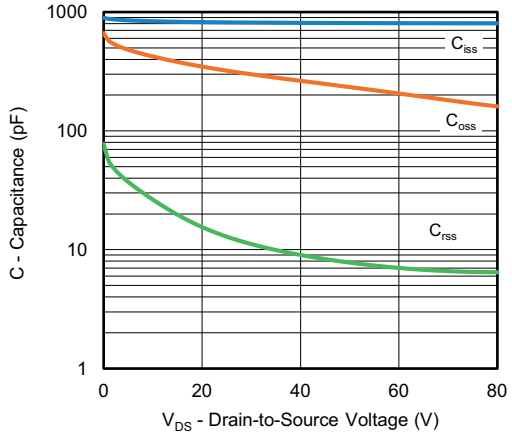
Output Characteristics



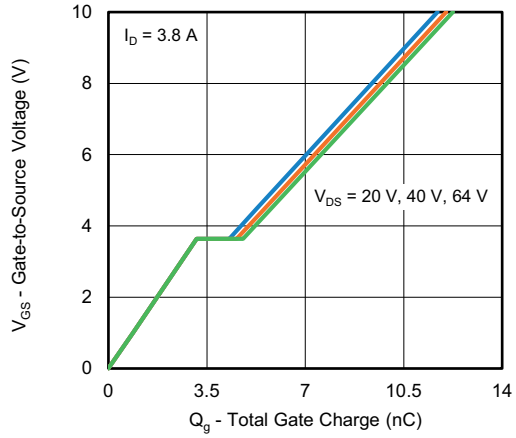
Transfer Characteristics



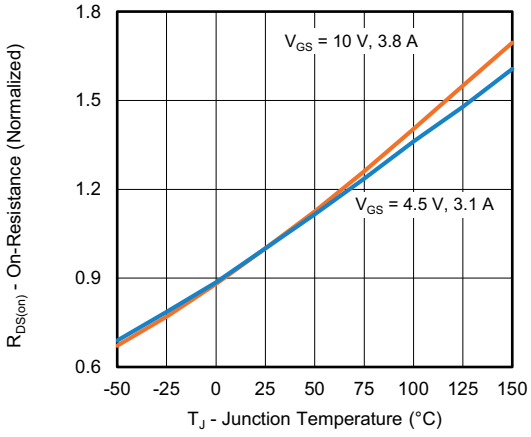
On-Resistance vs. Drain Current



Capacitance

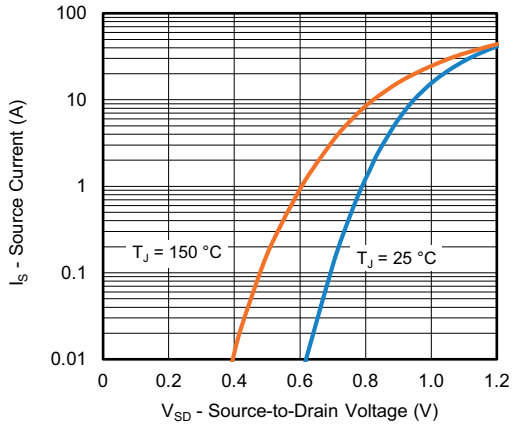


Gate Charge

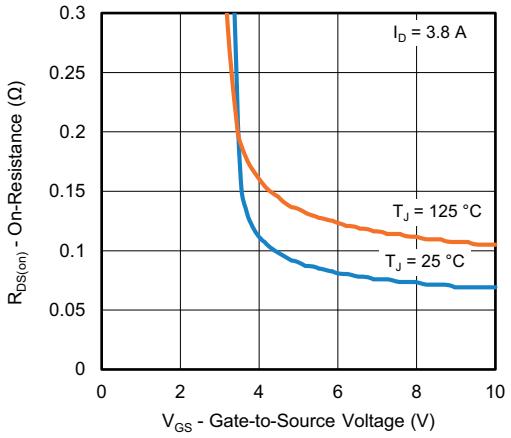


On-Resistance vs. Junction Temperature

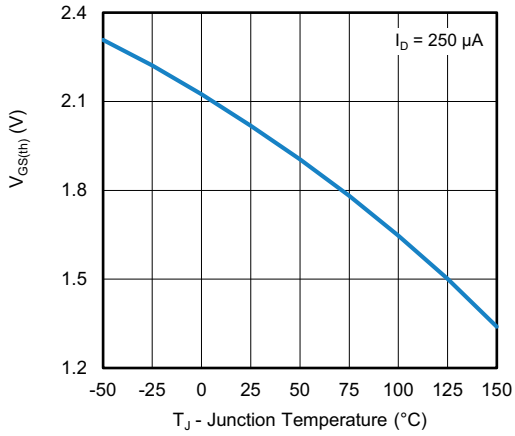
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



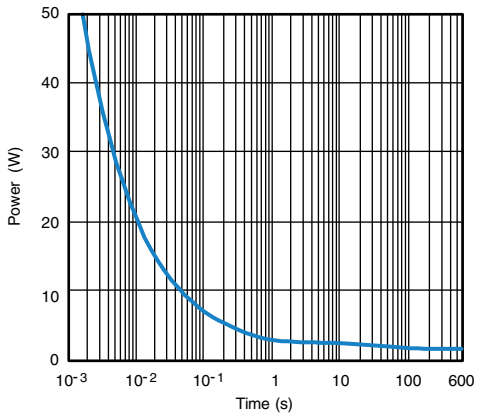
Source-Drain Diode Forward Voltage



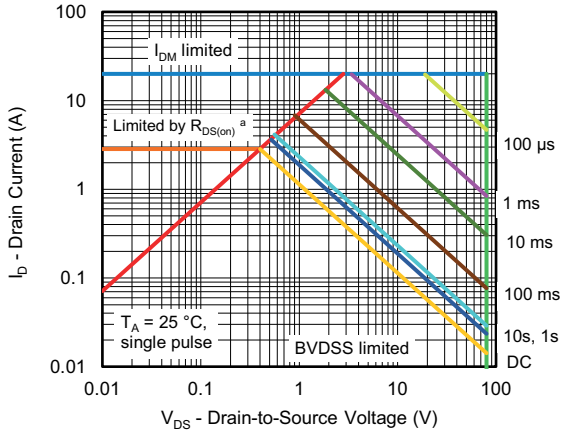
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

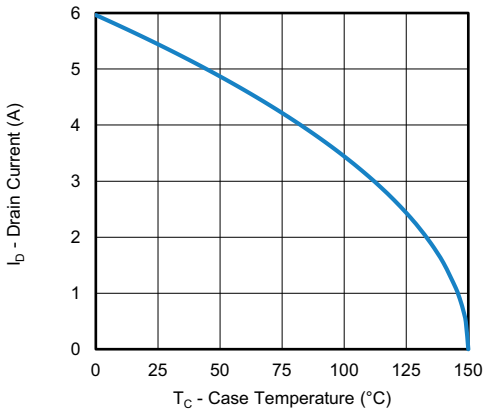


Safe Operating Area

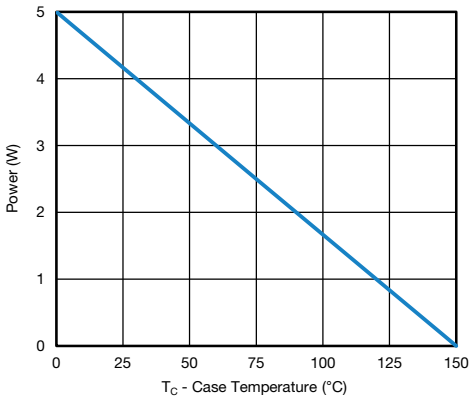
Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]

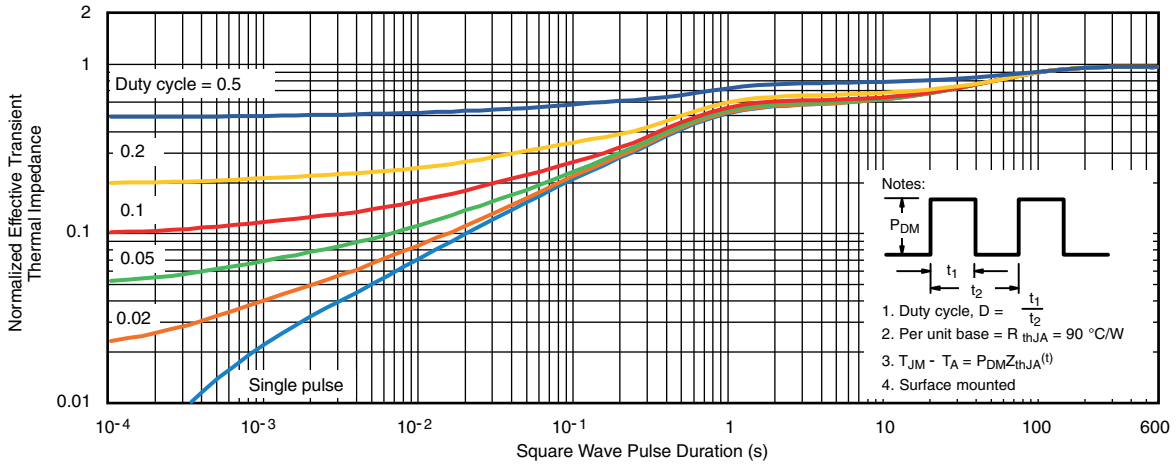


Power Junction-to-Case

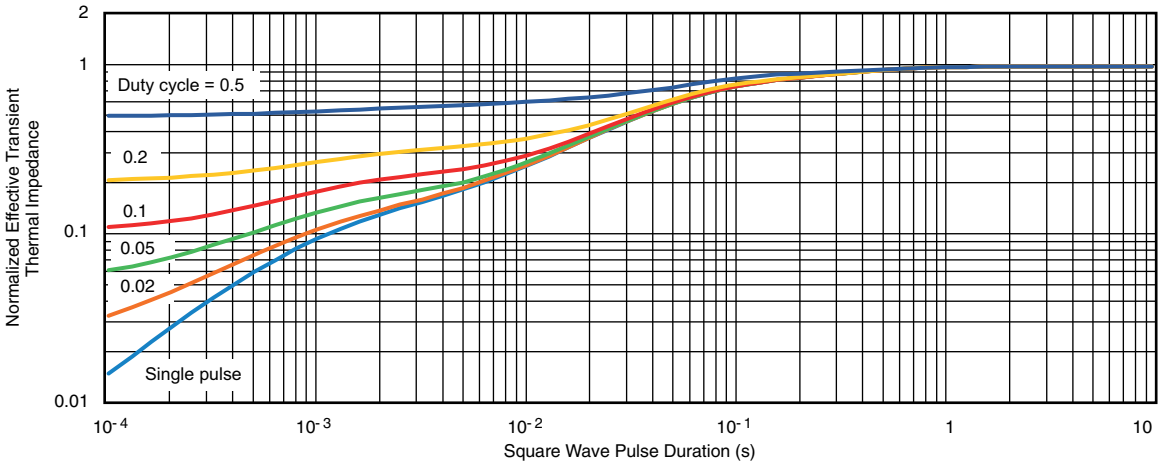
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



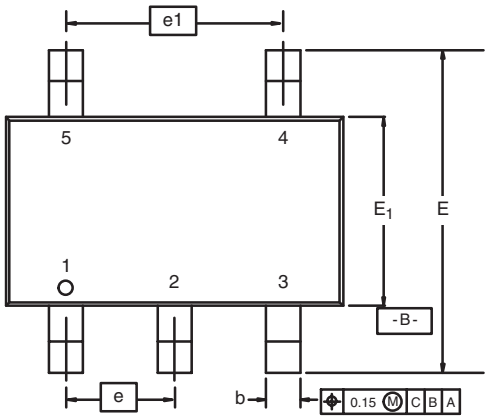
Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?78984.

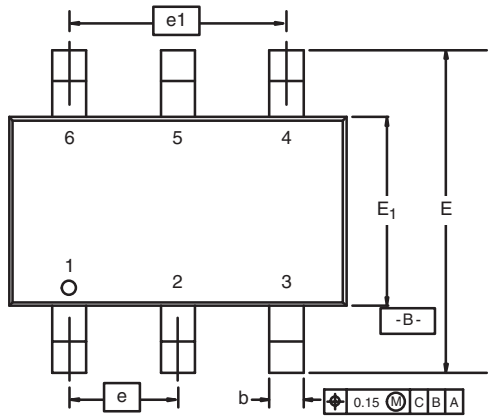
Package Information

Vishay Siliconix

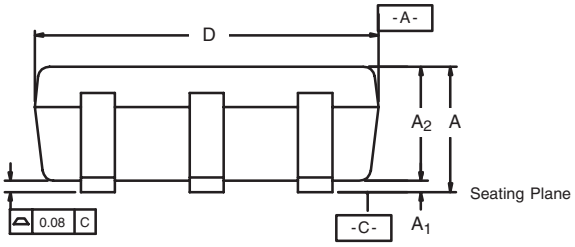
TSOP: 5/6–LEAD
JEDEC Part Number: MO-193C

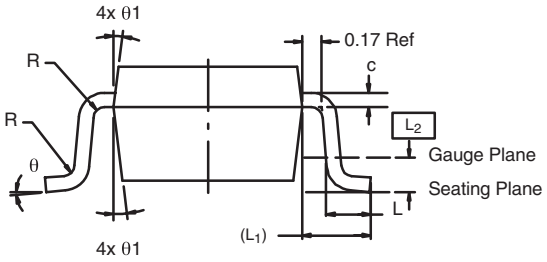


5-LEAD TSOP



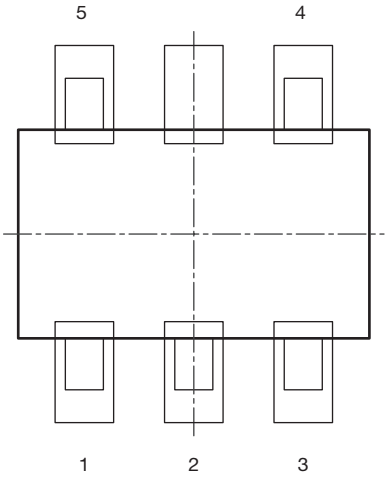
6-LEAD TSOP



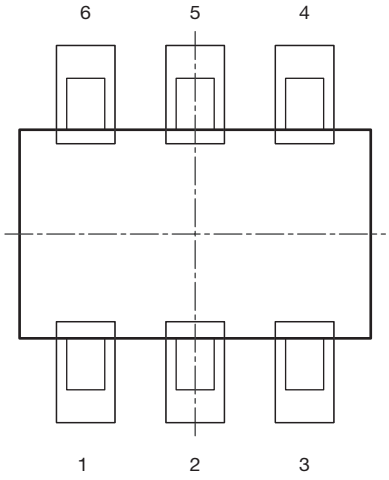


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A_1	0.01	-	0.10	0.0004	-	0.004
A_2	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E_1	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e_1	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L_1	0.60 Ref			0.024 Ref		
L_2	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

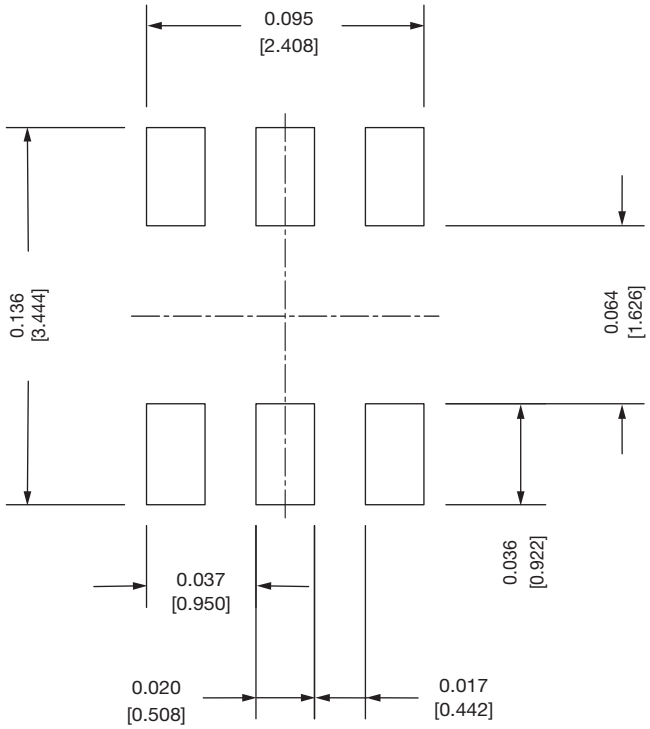
Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010

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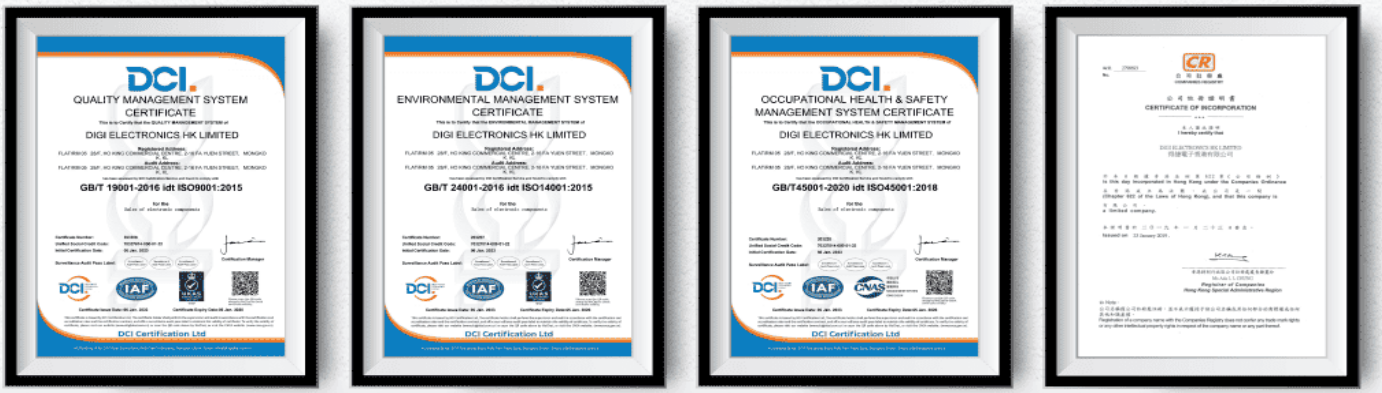

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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